

Development of a 500 kV DC Gun with Narrow Gap

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Outline

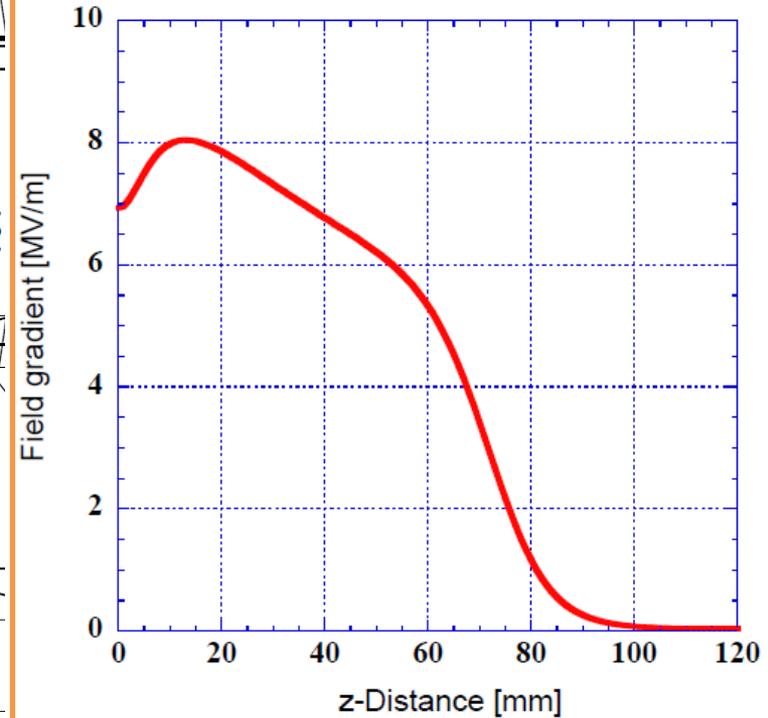
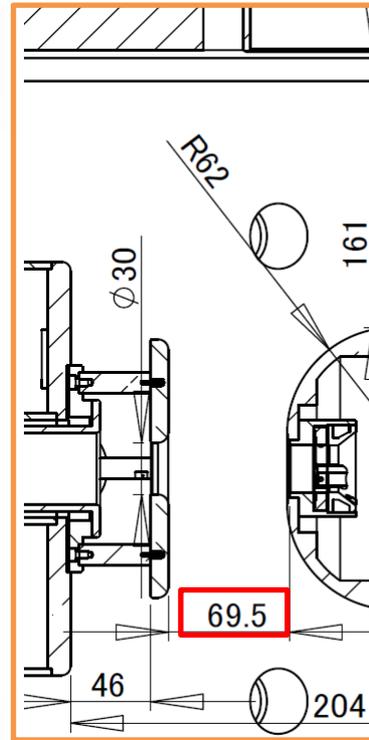
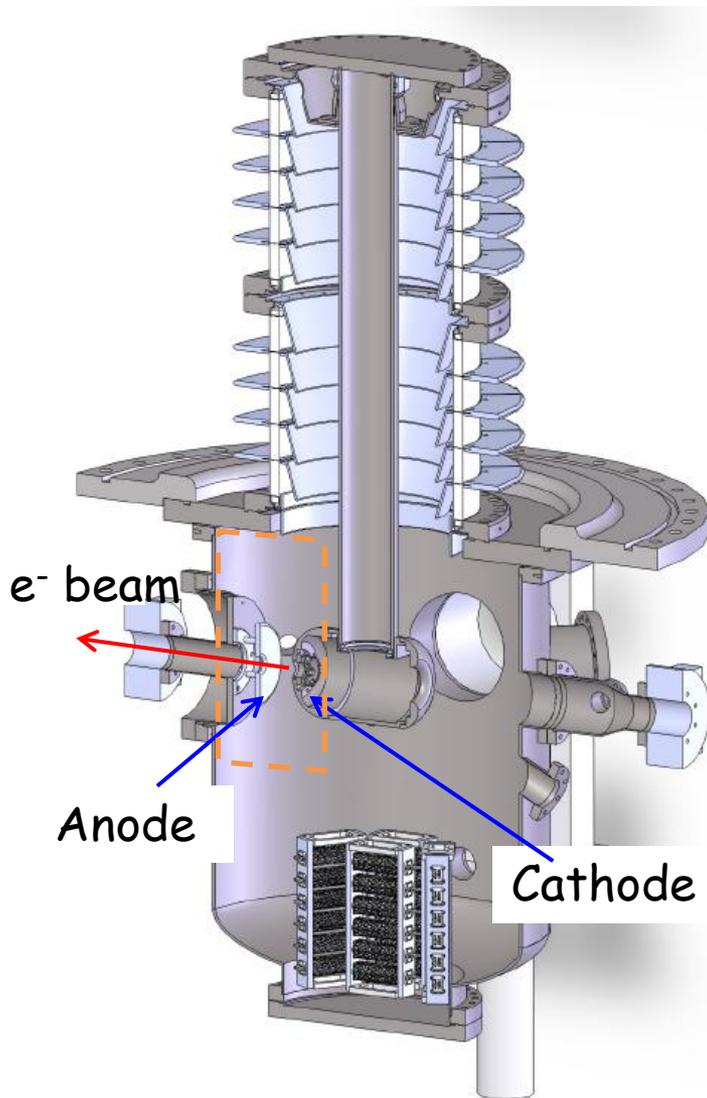
- Introduction
 - Gun basic configuration
 - Extreme high vacuum systems & baking

- HV test
 - FE problem
 - Conditioning & HV holding test
 - Model of trip voltage increase

- Photocathode preparation & installation
 - Cathodes simultaneous activation system
 - FE problem

- Summary

70 mm Gap 500 kV DC gun (2nd 500 kV gun) @KEK



$$\epsilon_n \propto \sqrt{q \cdot \frac{k_B T}{E_{\text{cath}}}}$$

- ✓ 6.9 MV/m @ photocathode center (=E_{cath})
- ✓ 11.0 MV/m @ cathode ball surface

Last 2 years progress (from ERL2013)

- ✓ Baking with main pump system.
- ✓ HV conditioning in XHV (4 times).
2014/May, /Jul, /Aug, 2015/Jan.
- ✓ Beam transport & Dump set up.

Oil-impregnation
Cockcroft-Walton
600kV HVPS

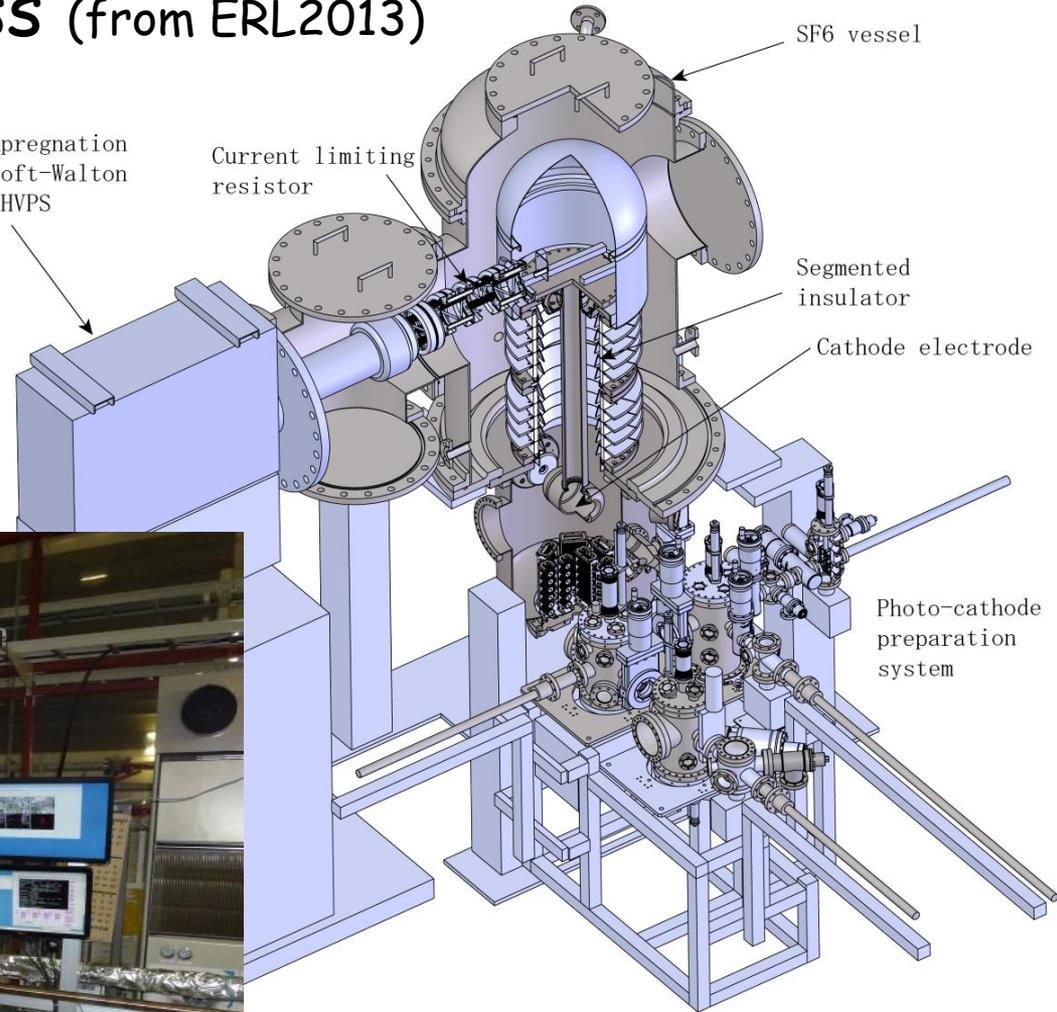
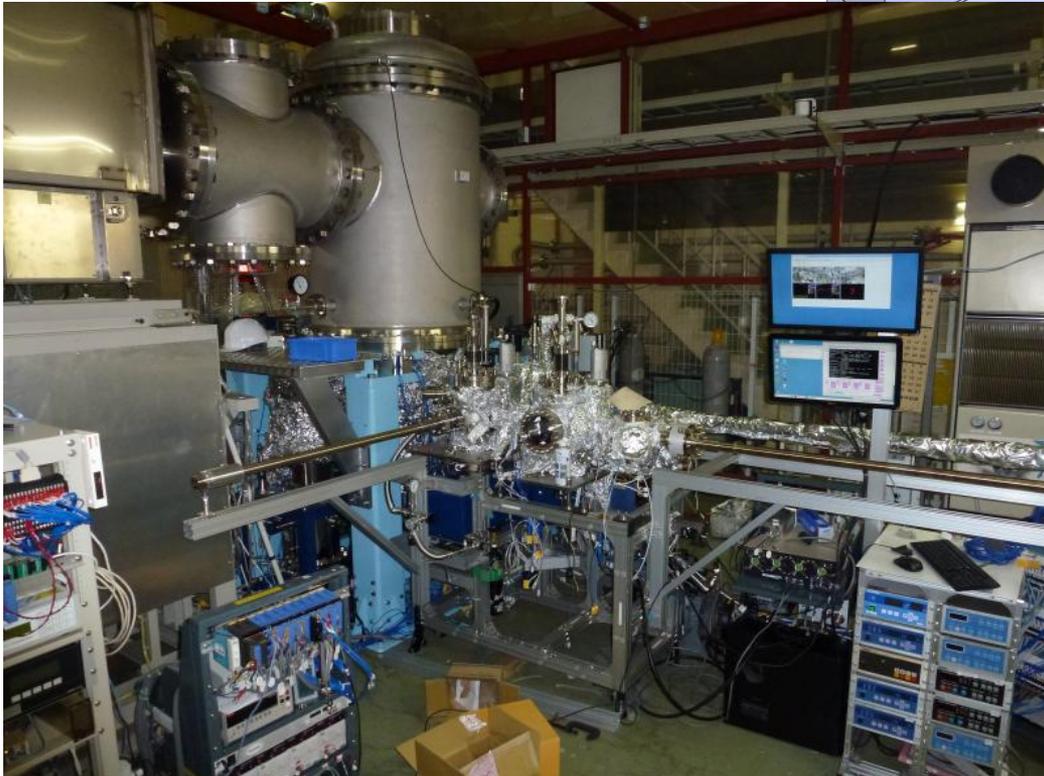
Current limiting
resistor

SF6 vessel

Segmented
insulator

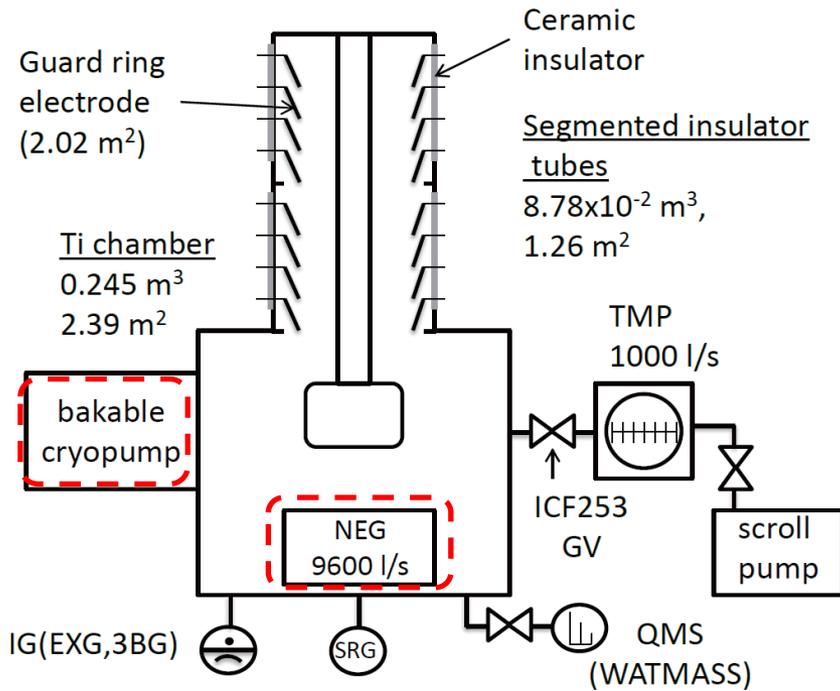
Cathode electrode

Photo-cathode
preparation
system



- ✓ Demonstrated 3 cathodes simultaneous activation.
- ✓ Connected cathode preparation system to the gun.

Main pump installation (2014/Mar)



Main pump composition

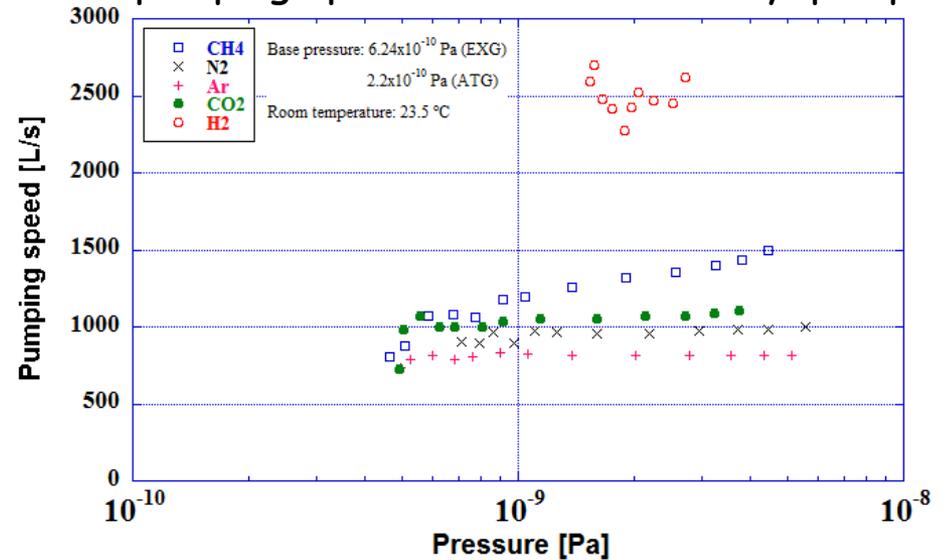
1. Non Evaporable Getter (NEG)

$$\begin{aligned} \text{D400-2} \times 24 &= 9600 \text{ L/s (H}_2\text{)} \\ &= 4320 \text{ L/s (CO)} \\ &\text{(catalog value)} \end{aligned}$$

2. 4K bakable cryopump

$$\begin{aligned} &\sim 800 \text{ L/s (Ar)}, \sim 1000 \text{ L/s (N}_2\text{, CO}_2\text{)}, \\ &\sim 1200 \text{ L/s (CH}_4\text{)} \text{ (measured values@}1 \times 10^{-9} \text{ Pa)} \end{aligned}$$

pumping speed of 4K bakable cryopump

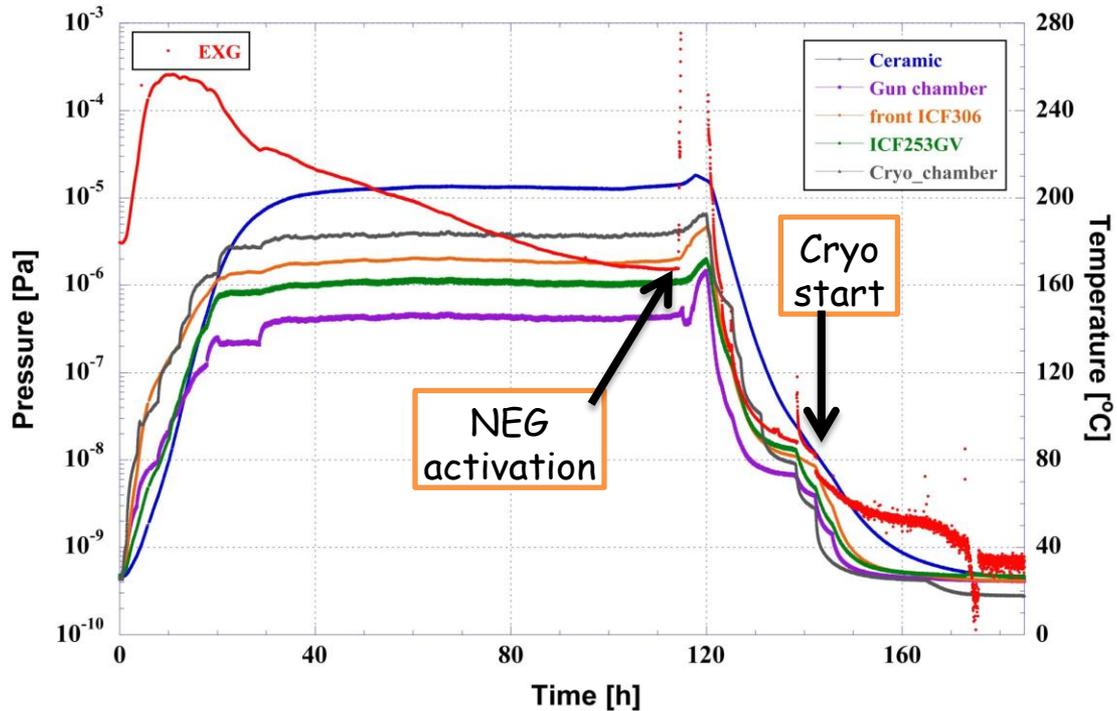


NEG pump set

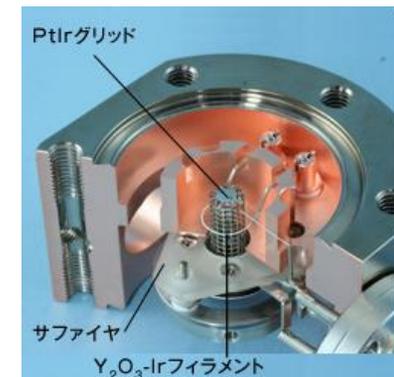
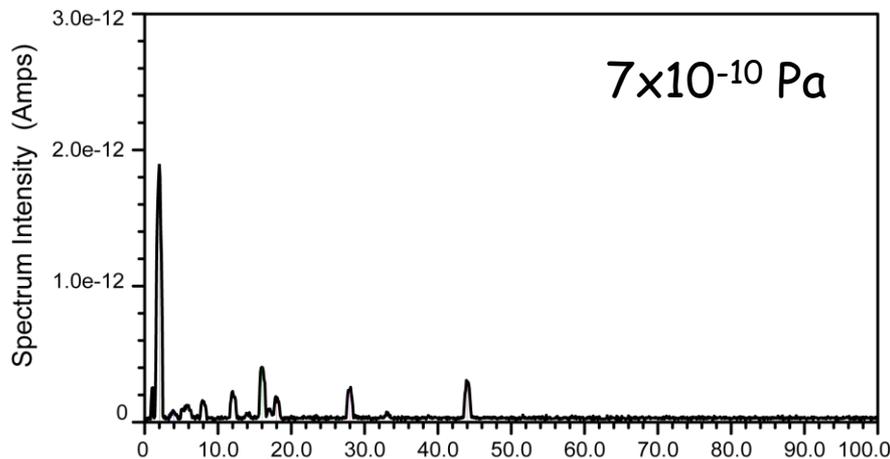
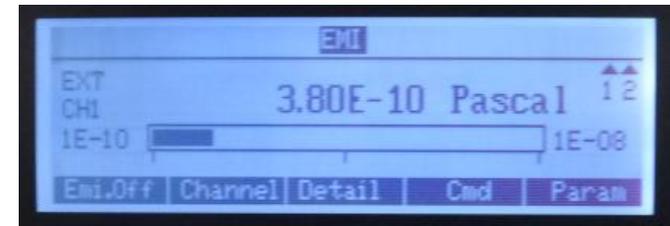


4K bakable cryopump

Baking & RGA spectrum in XHV (2014/Mar~Apr)



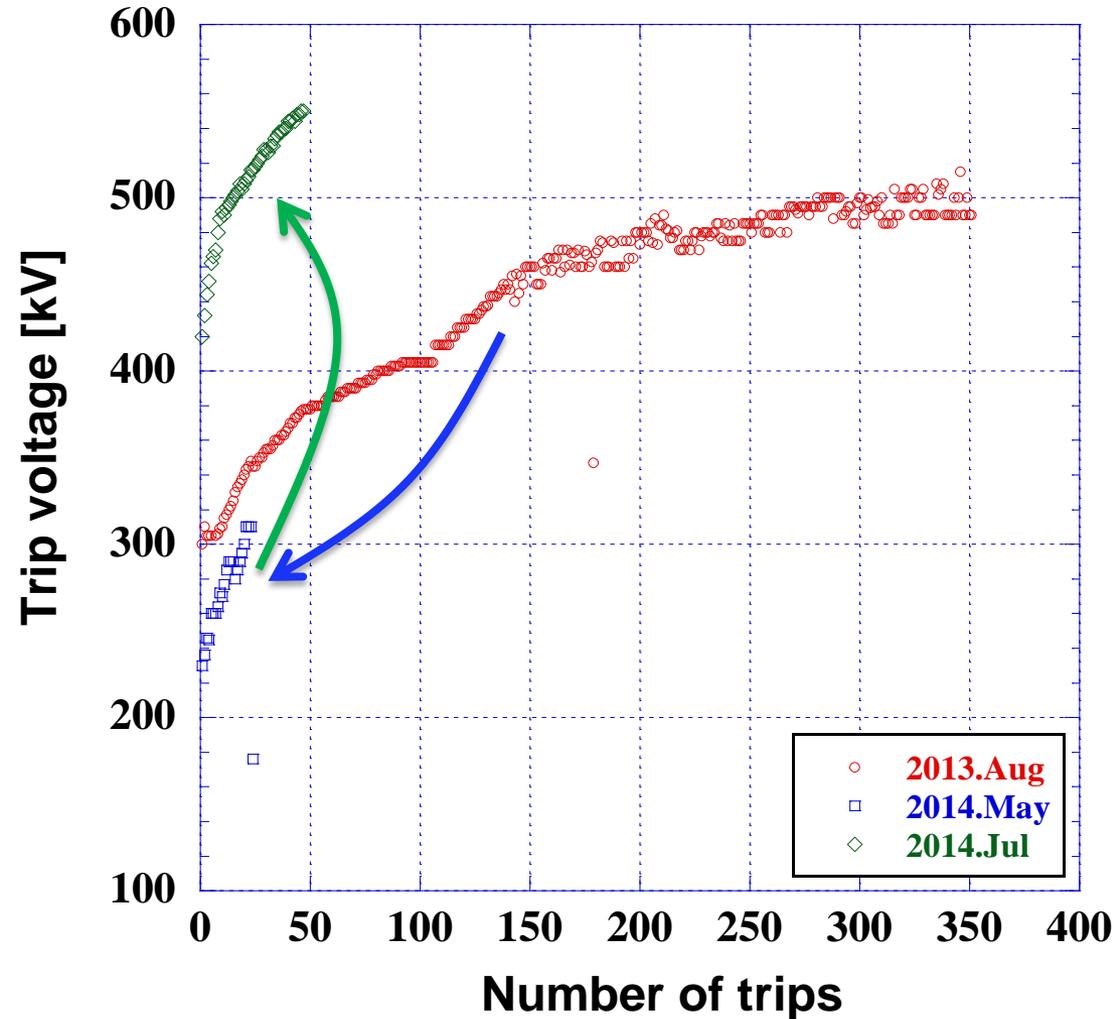
3B Gauge



Special RGA ion source for XHV

<http://www.vaclab.co.jp/product04.html>

HV conditioning history (2013/Aug ~ 2014/Jul)



2013/Aug. HV Conditioning
(w/o main pump system)
reached 500 kV after ~300 trips



Main pump installation & baking.
XHV ($\sim 4 \times 10^{-10}$ Pa) achieved.

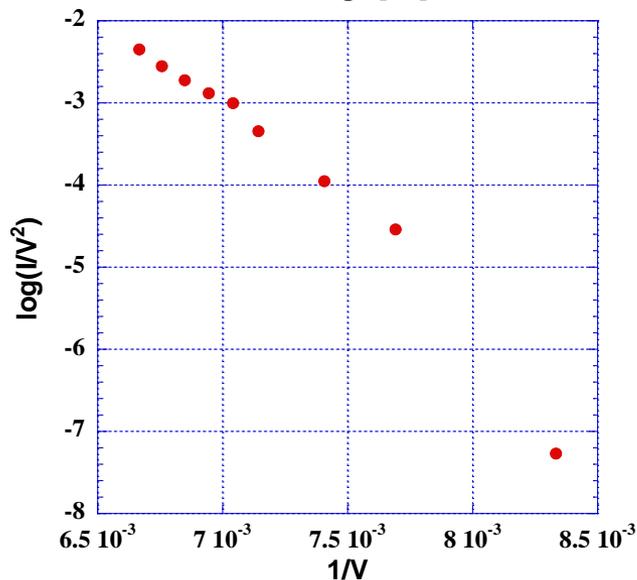
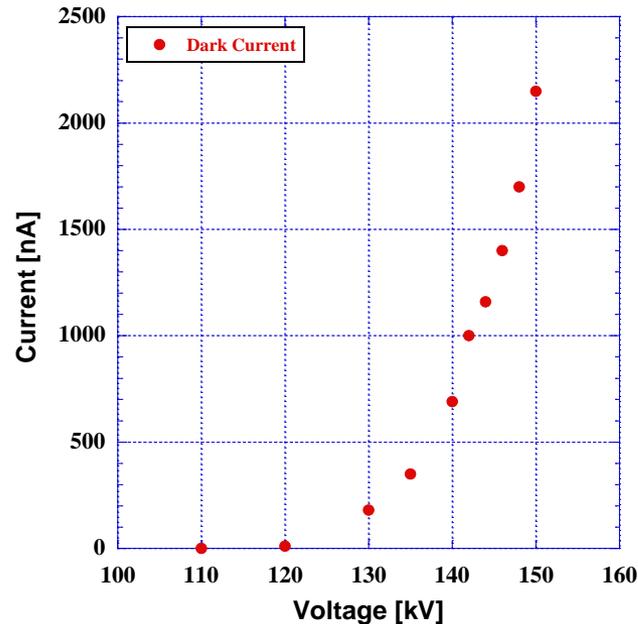
2014/May HV Conditioning
(FE source was generated after 24 trips)



Took off electrode & eliminated
dust on the cathode electrode.
Set electrode and baking &
rebuilt HV setup again.

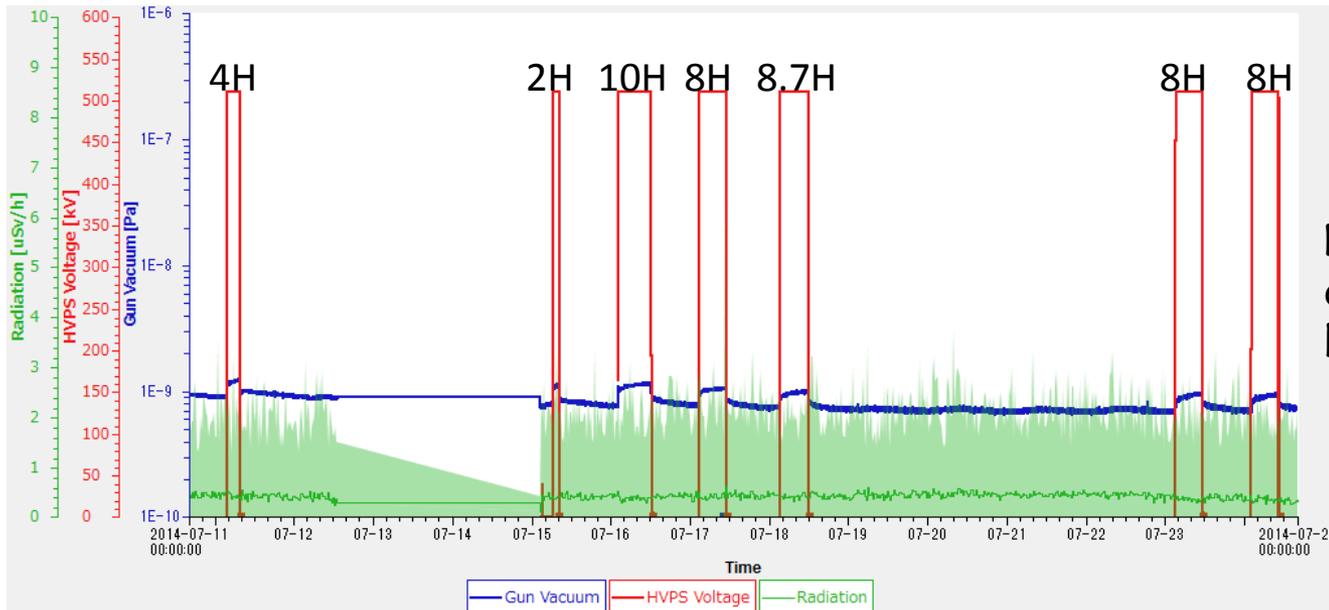
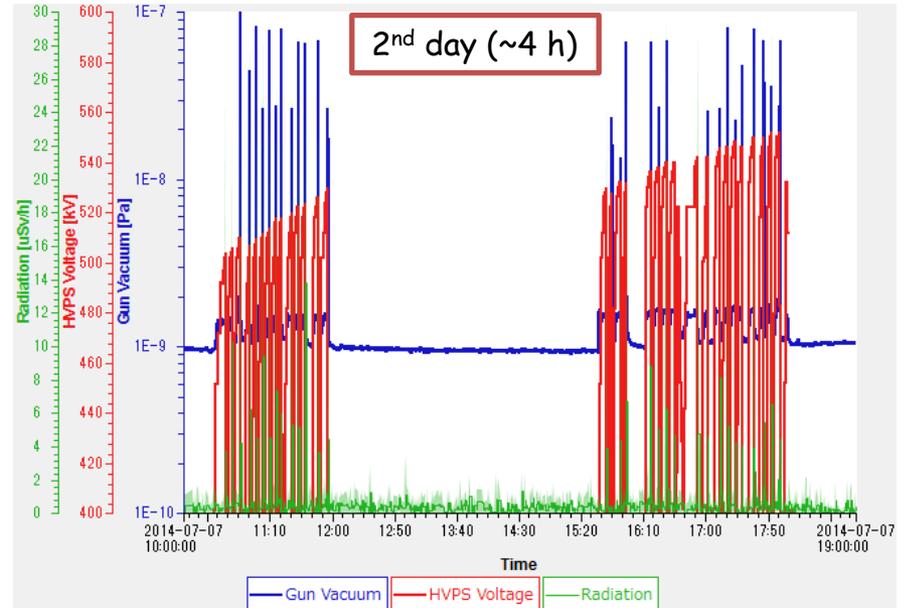
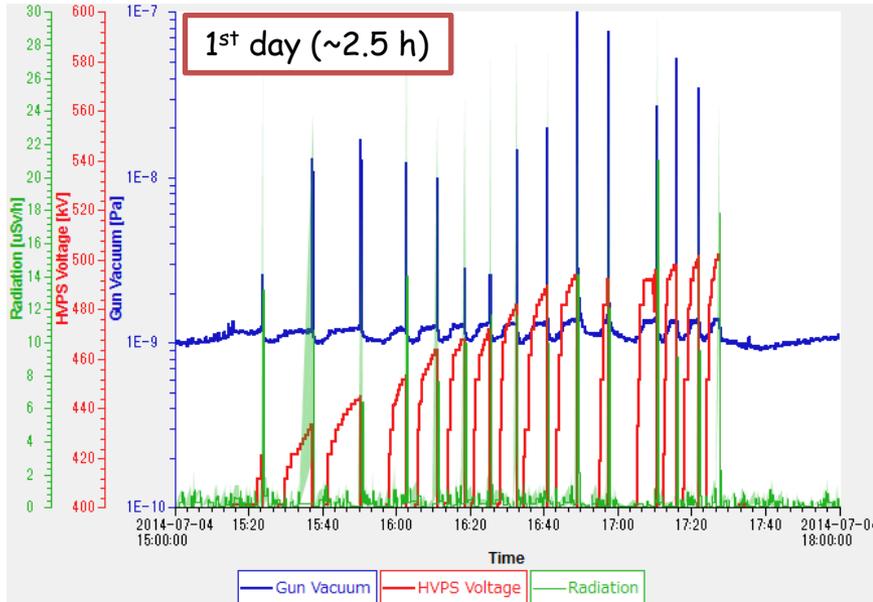
2014/Jul. HV Conditioning
(reached 550 kV after 48 trips)

Field emission from a dust (2014/May~Jun)



The dust was easily vanished by blowing ionized air.
Finally, the electrode was cleaned by wiping lint free cloth. (with ethanol& dry cloth)

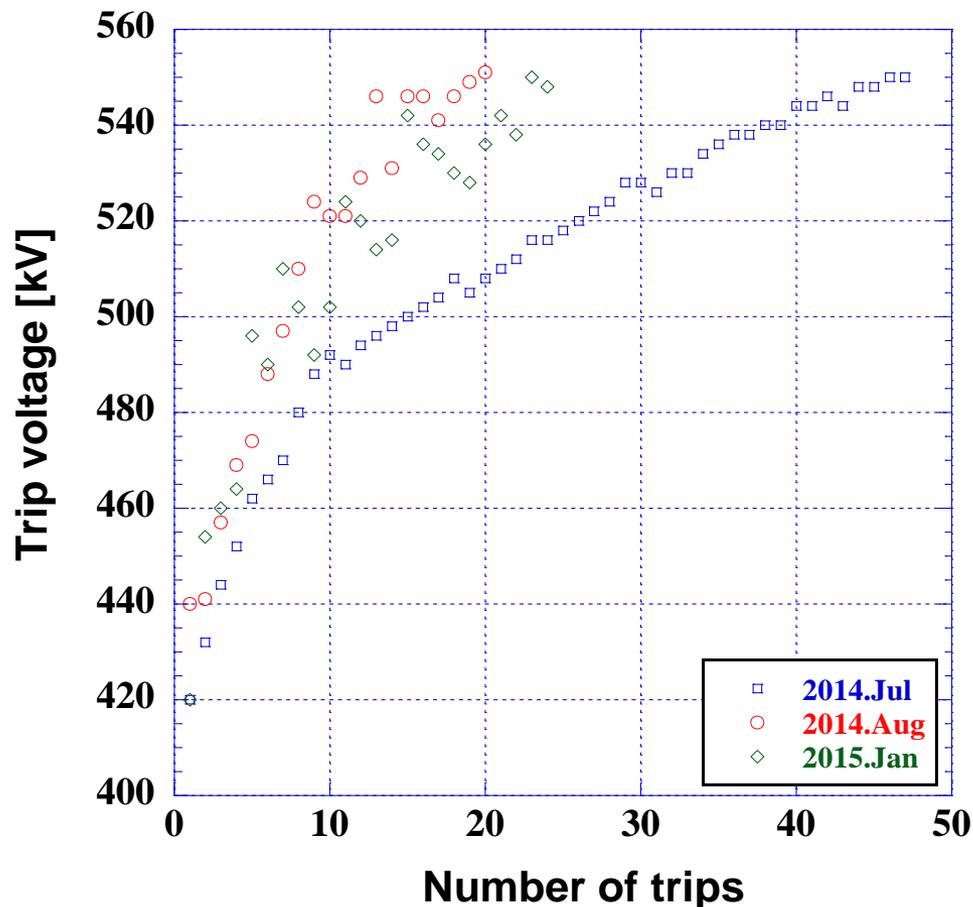
HV conditioning & holding test (2014/Jul)



HV conditioning was finished in a short time (~7 hours).

No breakdown happened during 50 hours 500 kV-holding test.

HV conditioning repeatability (2014/Jul ~ 2015/Jan)



2014/Jul. HV Conditioning
(reached 550 kV after 48 trips)

~3 weeks shutdown
~1 week for XHV establish

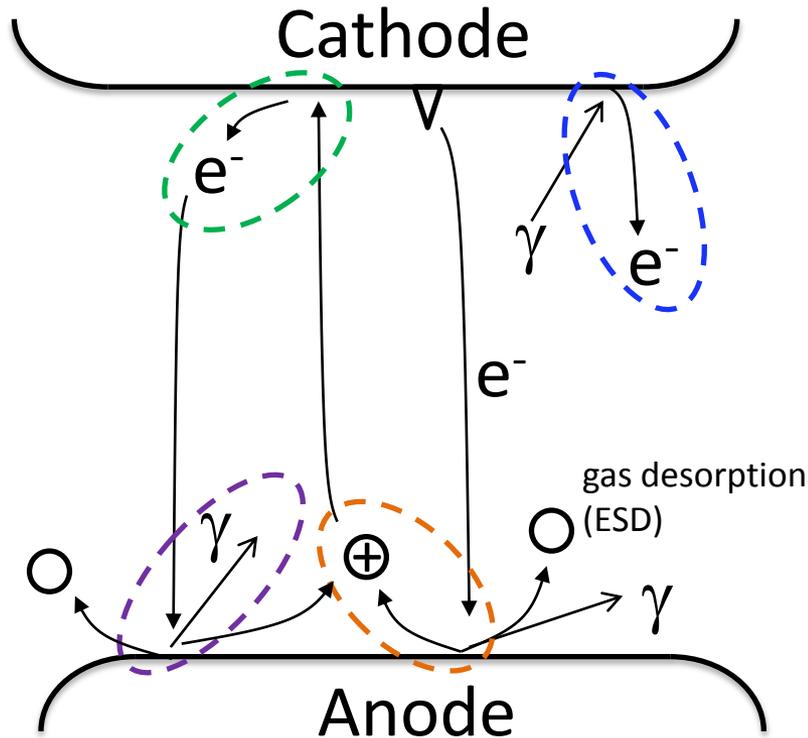
2014/Aug. HV Conditioning
(reached 550 kV after 20 trips)

~3.5 months shutdown
~1 week for XHV establish

2015/Jan. HV Conditioning
(reached 550 kV after 23 trips)

Almost trip events were hardly detected emission current (≤ 1 nA) just before trip happened. Almost trip voltage increased continuously as if the trip voltage was memorized. How we can explain this ?

Breakdown process in vacuum gap



Four essential coefficients (A~D)

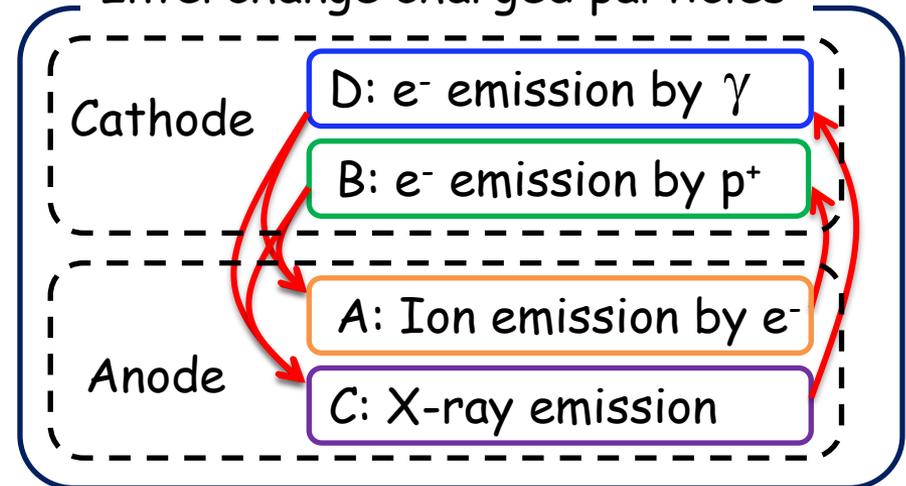
- A: Electron induced ion emission
- B: Ion induced electron emission
- C: Photons produced by a electron
- D: Electron produced by a photon

J.G.Trump & R.J. van de Graaff, J. Appl. Phys.
18, (1947) 327

In case of ...

- * DC bias in UHV.
- * small dark current condition.
(a small seeding for breakdown process)

Interchange charged particles



$$\underline{\text{avg}(A*B+C*D) > 1}$$

Discharging & Vacuum trip.

$$\underline{\text{avg}(A*B+C*D) < 1}$$

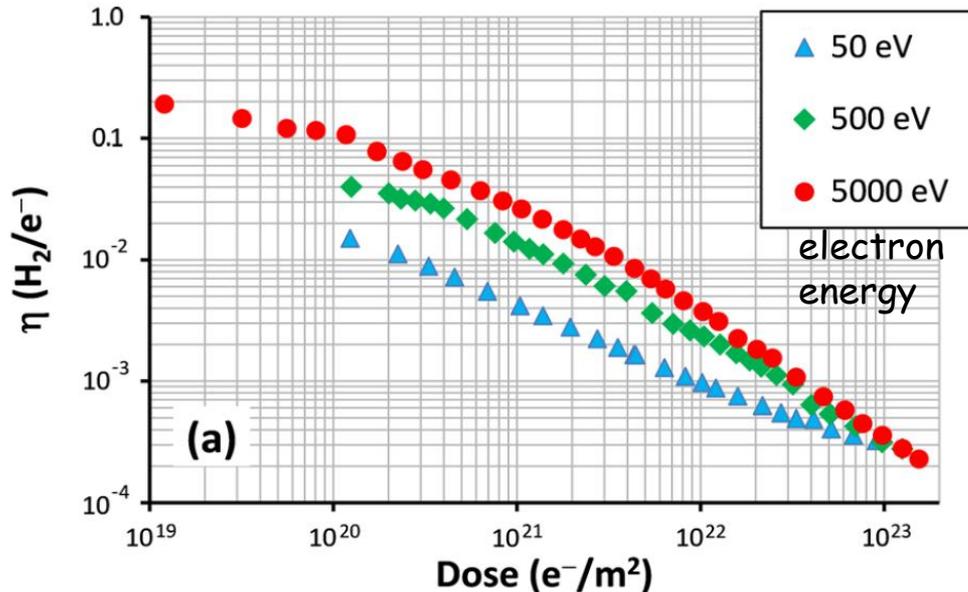
Finished discharge phenomenon

Model of trip voltage memory phenomenon

Electron induced ion (H^+ , H_2^+ , etc.) emission is probably related electron stimulated desorption (ESD) phenomenon.

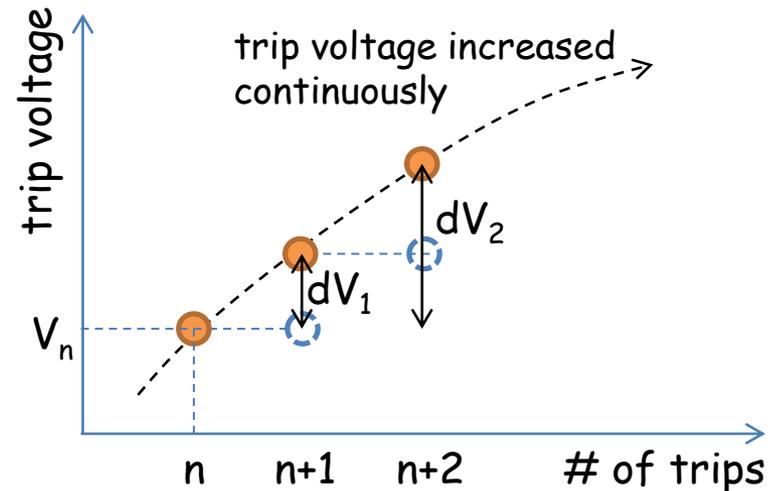
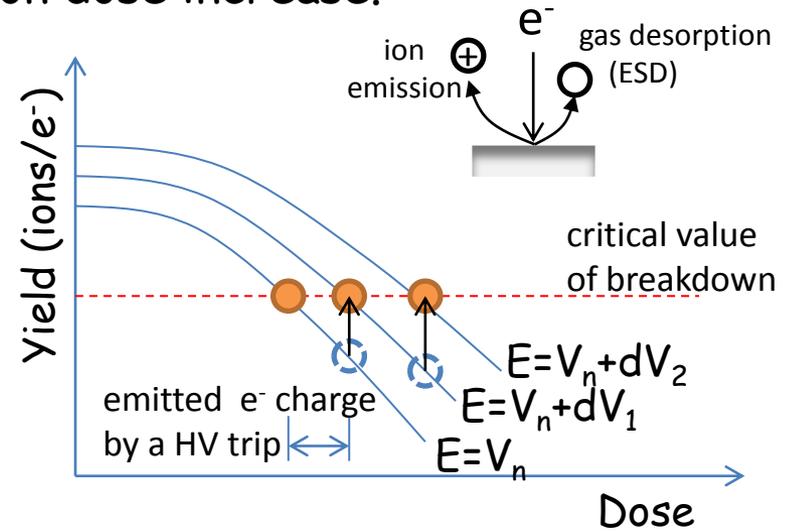
ESD yield is decrease drastically by electron dose increase.

Hydrogen desorption from SUS316L



Oleg B. Malyshev et al., J. Vac. Sci. Technol. A 31 (2013) 031601

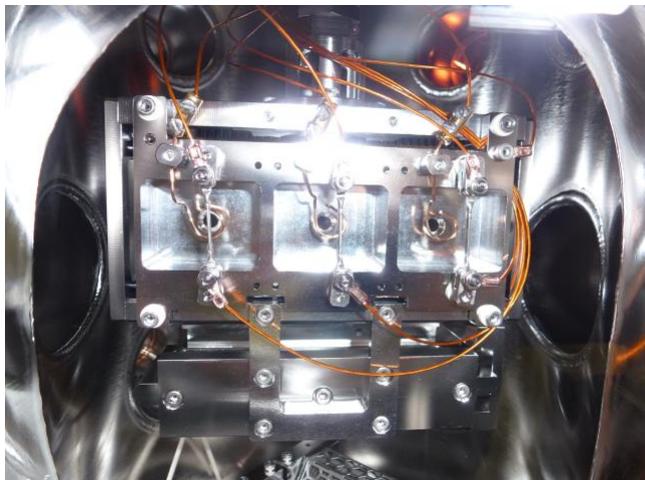
- ✓ ESD property of anode surface may give a important hint to know a limitation of breakdown voltage.



Cathode preparation system

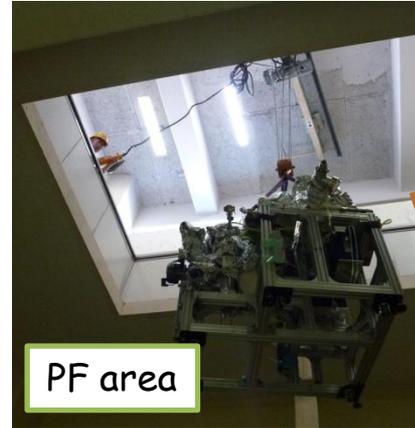


Three cathodes simultaneous activation (QE:6~10%) were successful. (2014/Sep.)



Inside view of activation chamber

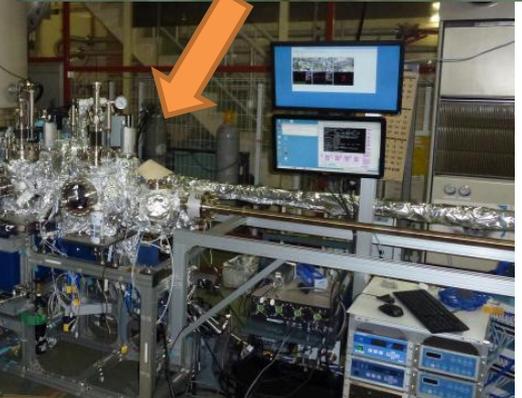
Last cathodes-activation was done in 2015/Jan. and transported to the storage chamber. ~2 months storage cathode was still alive.



PF area

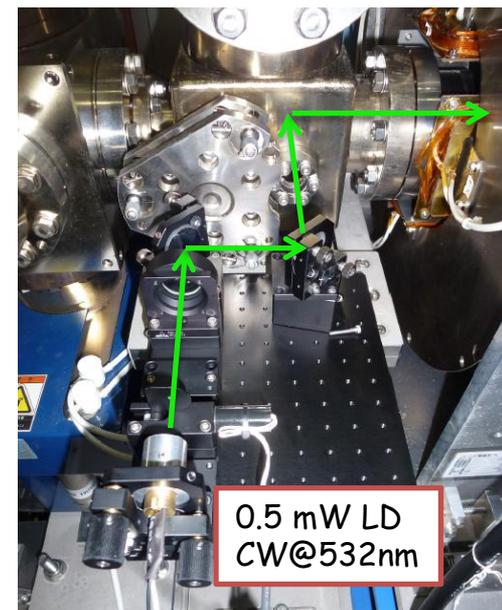
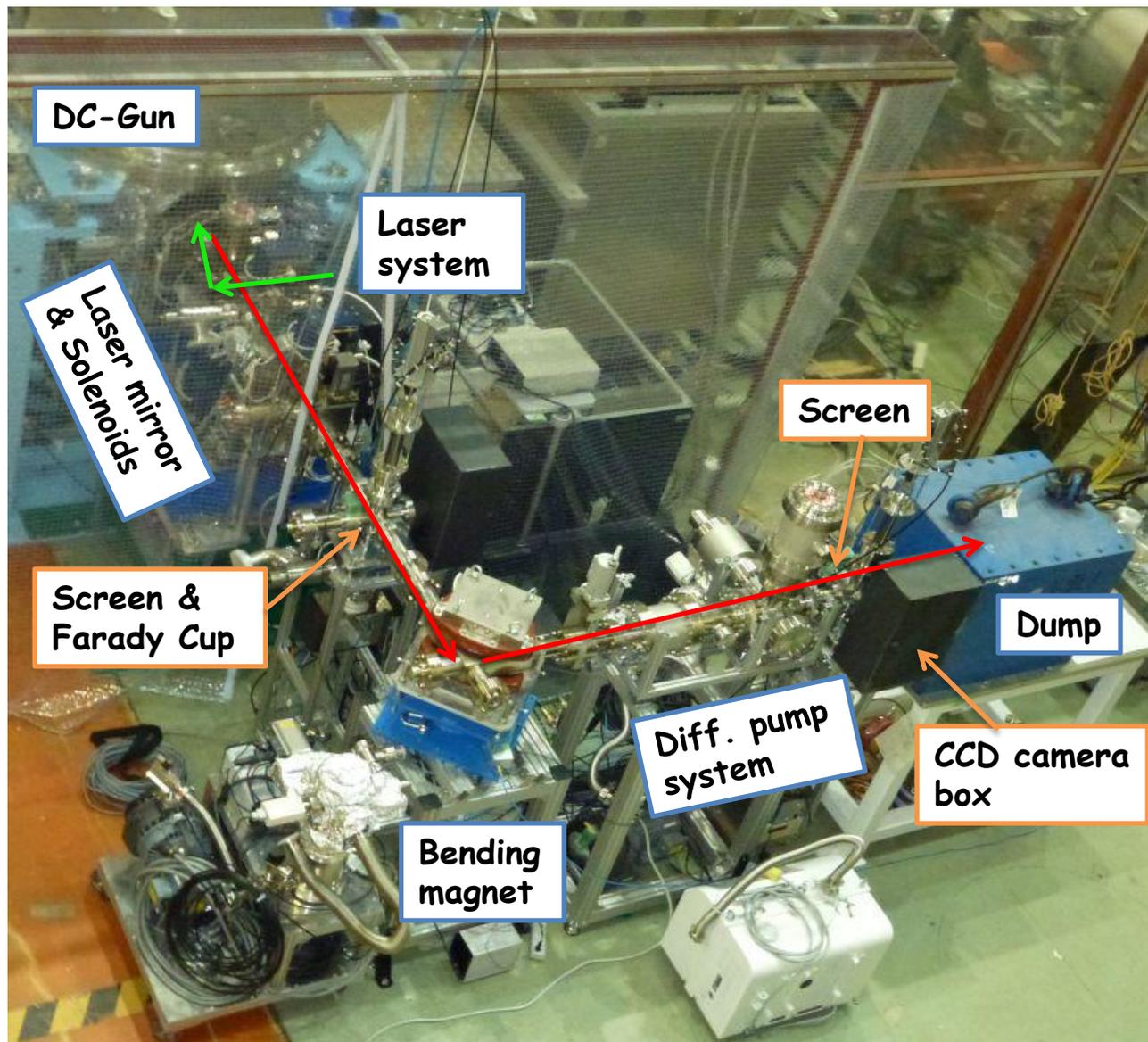


GTF area

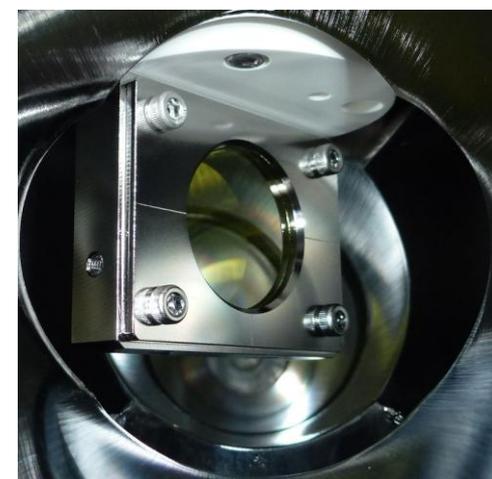


The prep. system was moved 2014/Oct. Reconstruct & connected to the gun 2014/Nov~Dec.

Beam Transport & Dump section

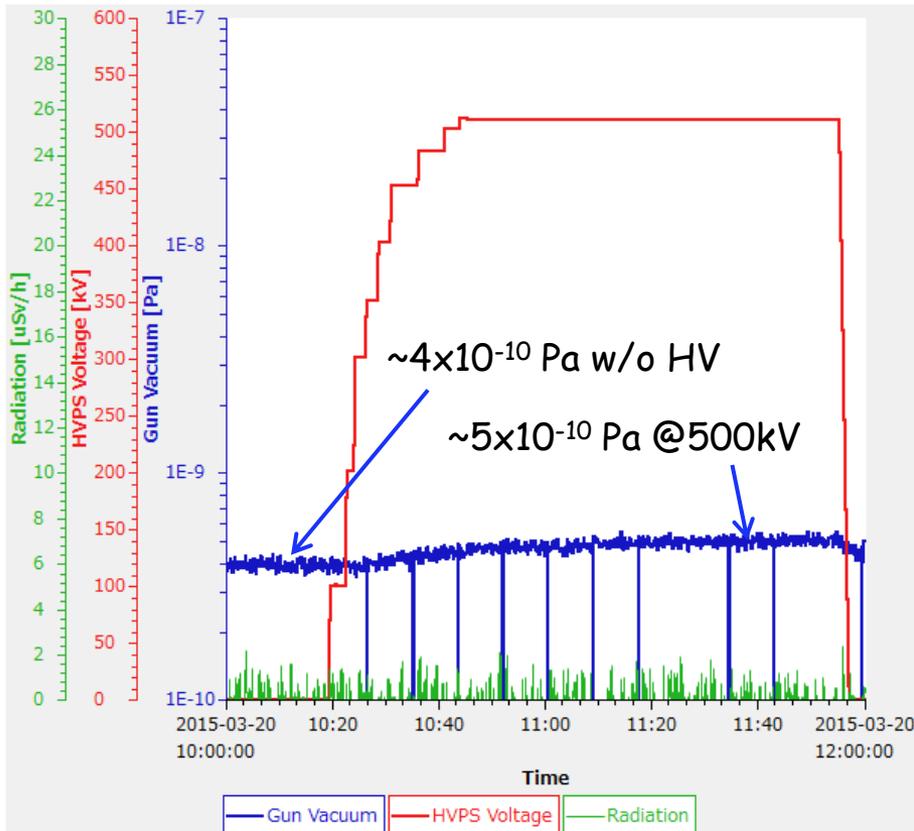


Laser system



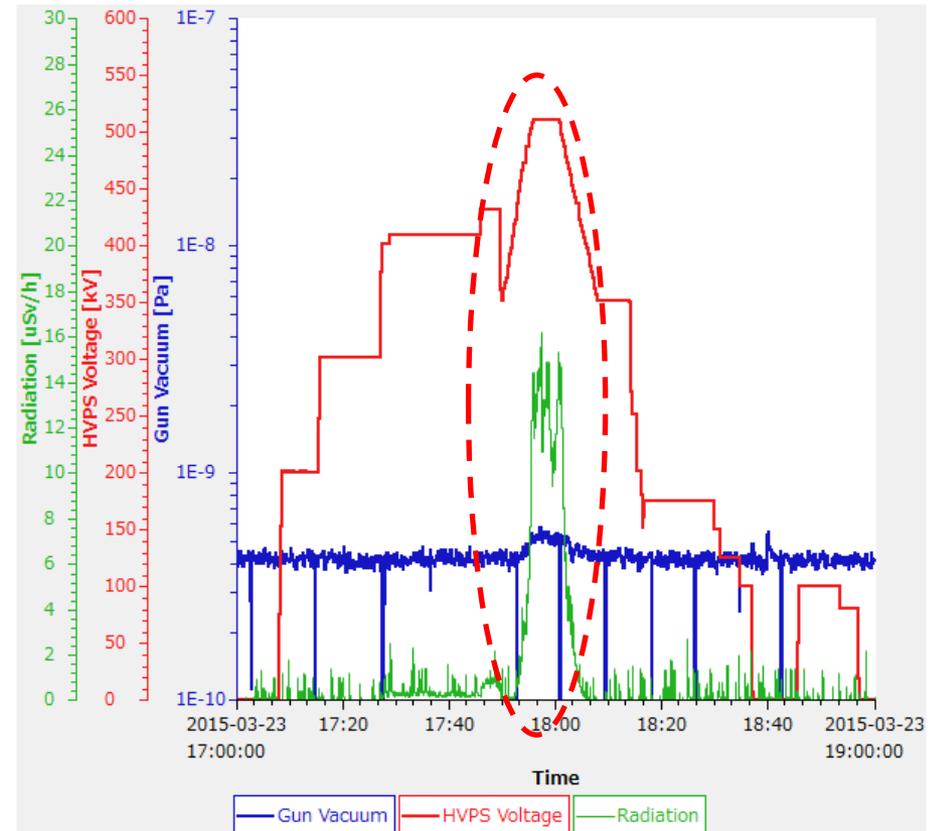
YAG screen

Field emission problem by cathode installation



Before photocathode installation
(Equipped with SUS dummy puck)

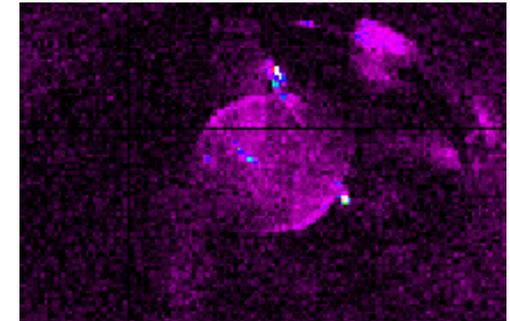
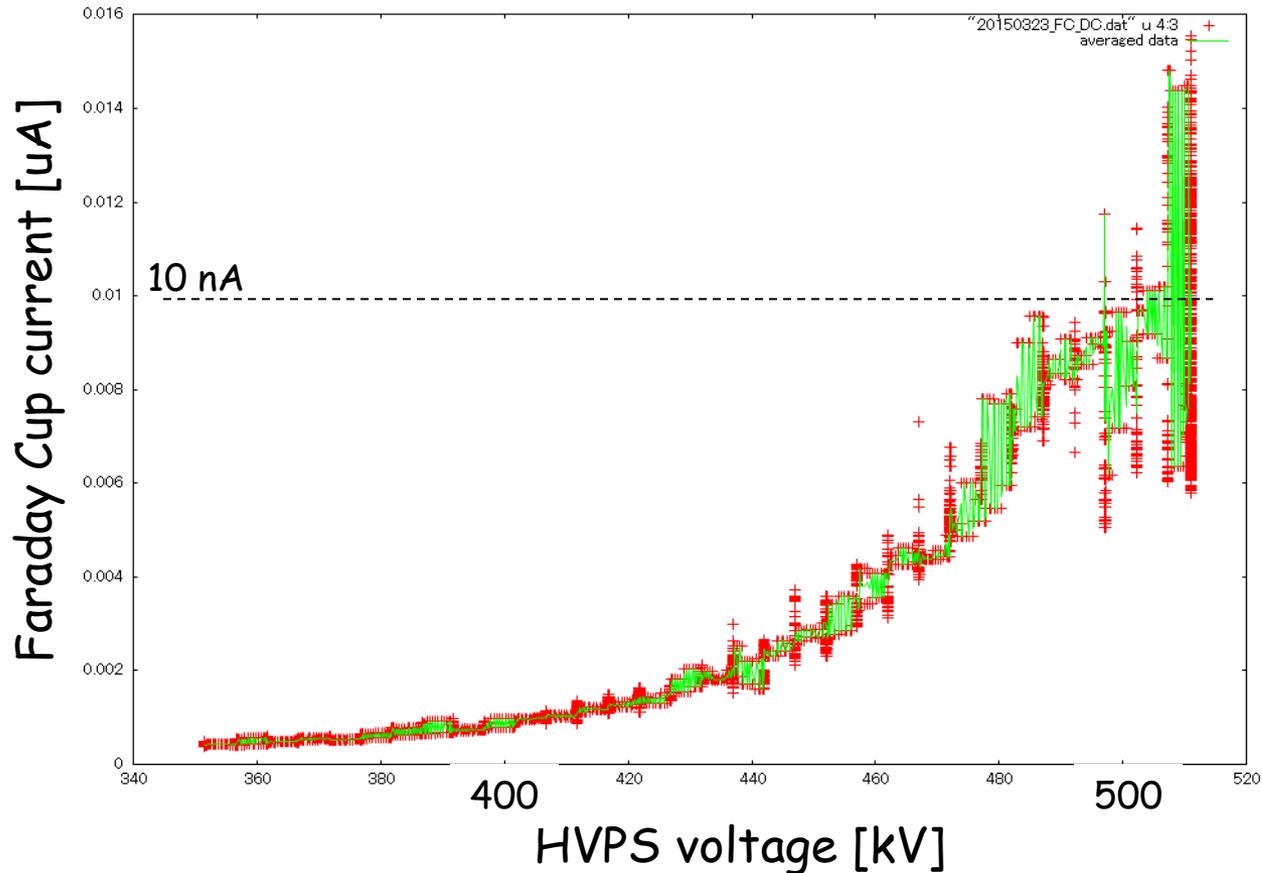
Only BG level radiation, dark current (<1 nA) were detected under a 500 kV condition.



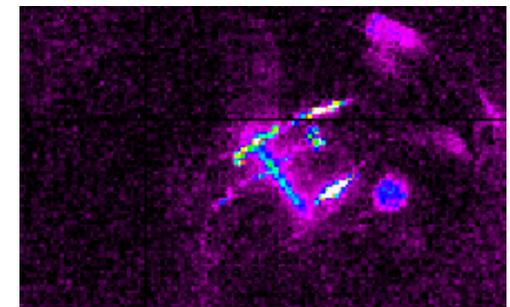
After activated photocathode installation
(Bulk GaAs)

About 15 uSv/h radiation, ~ 4 nA dark current to anode electrode were detected under a 500 kV condition.

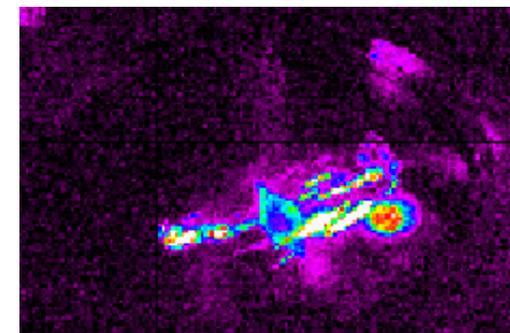
Dark current beam profile (w/o laser irradiation)



350 kV



400 kV



450 kV

Photoemission by stray light of ion gauge was exist.
(< 0.5 nA)

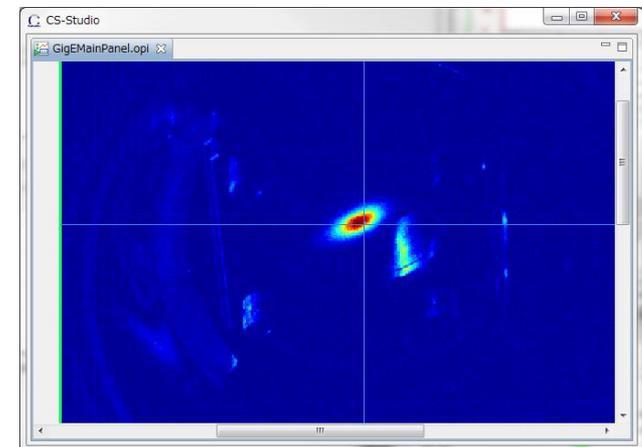
Some field emitters exist near the photocathode.
Field emission current was increased when the gun
voltage over 400 kV.

Summary

- Extreme high vacuum was established by NEG & bakable cryopump.
- HV conditioning up to 550 kV & 50 hours holding test of 500 kV were successful.
 - Fortunately, FE problem was solved by easy way.
- A model of trip voltage memory mechanism was proposed.
- Cathode preparation system was constructed.
 - Three cathodes simultaneous activation was successful.
 - ~2 months storage cathode was alive.
- Unfortunately, FE problem was come back by a cathode installation.
 - Investigations of FE source & the point at issue are underway.

Now & Feature plan

- 400 keV beam study is just started.
- Preparations for mA class high current cw-beam operation are underway.
 - Radiation shield
 - Water cooled beam dump
 - Fast interlock system



400 keV beam profile near the dump
(with laser irradiation)

Acknowledgement

H. Iijima for construction beam transport & dump line and many wiring works.
 T. Michikawa, S. Nagahashi, R. Takai and T. Obina for making a lot of IOC programs and many advices about devices control.
 F. Watanabe for advice of XHV measurements.

CSS
 Cathode_control.opi cathode_cleaning.opi cathode_activation.opi

Cathode Preparation System Control Display ver.0 2014/07/30 11:48:01

Reload PREP_STAT_LAST
 Save VAC_Status
 Open Cathode_db.opi
 Open Prep_history.opi

Vacuum Suitcase 1.00E-9 Pa empty empty empty
 Set new cathodes Move to Storage Eject cathodes

Storage chamber
 A-1 empty Mes empty C-1 empty
 A-2 empty B-2 empty C-2 empty
 A-3 empty B-3 empty C-3 empty
 A-4 empty B-4 empty C-4 empty
 A-5 empty B-5 empty C-5 empty
 A-6 empty B-6 empty C-6 empty
 8.17E-10 Pa Move to Gun Move to Act Move to VSC
 Change puck position Open QEmap.opi

Gun empty
 Disconnected
 Move to Storage

Act. chamber 7.52E-8 Pa 3.63E-7 Pa 1.56E-7 Pa
 A B C
 Move to Storage

Cleaning chamber 7.82E-9 Pa
 1 empty 2 empty 3 empty
 Open Activation.opi Move to CLEN or LOAD Change puck position

Loading chamber
 1 empty 2 empty 3 empty
 Open Cleaning.opi Set new cathodes Move to ACT Move to LOAD Move to CLEN Eject cathodes

Container Storage
 B C
 1 empty empty
 2 empty empty
 3 empty empty
 Change container position

TMP Vac.

